

Electronic supplementary information of
**Silicon nanocrystal hybrid photovoltaic devices
for indoor light energy harvesting**

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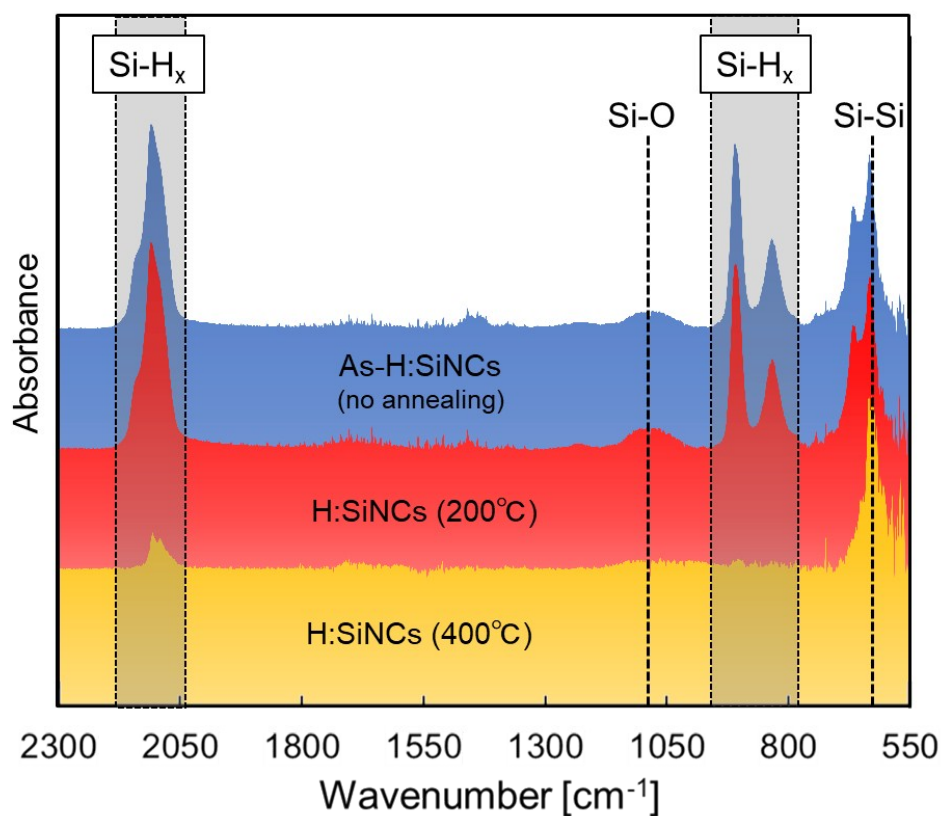


Figure S1. FTIR spectra of SiNCs before and after thermal annealing; as-H:SiNCs (no annealing), H:SiNCs (200 °C for 1 hour) and H:SiNCs (200 °C for 1 hour)

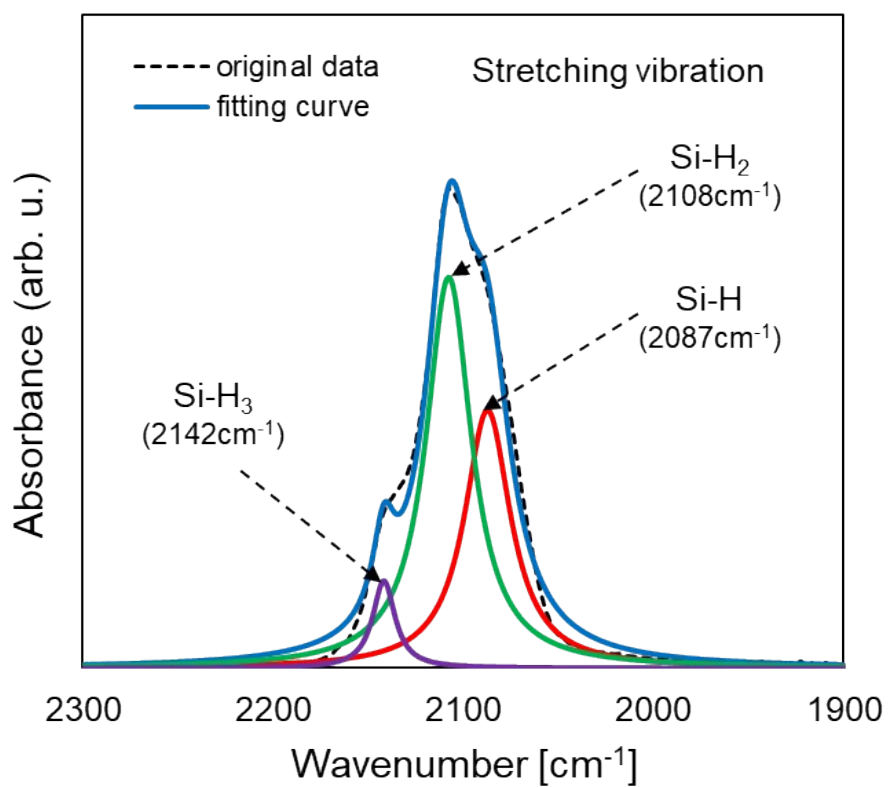


Figure S2. Deconvolution of SiH_n bonds on the as-H:SiNC (no annealing) surface